TAIWAN SEMICONDUCTOR

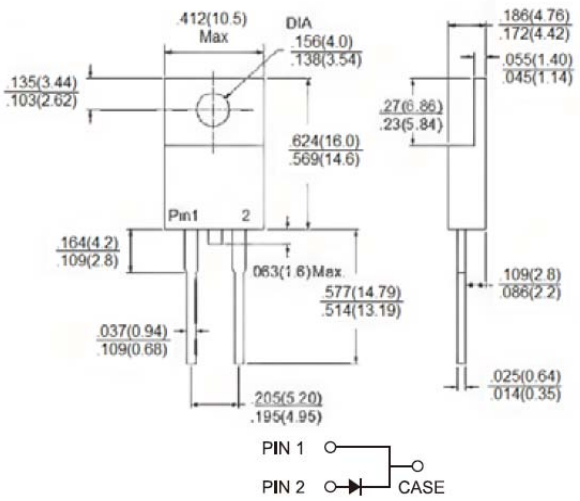
SFA801G - SFA808G

8.0AMPS Glass Passivated Super Fast Rectifier

TO-220AC

RoHS COMPLIANCE





Features

- ✧ High efficiency, low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ Low power loss
- ✧ For use in low voltage, high frequency inventor, Free wheeling, and polarity protection application
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode

Mechanical Data

- ✧ Case: TO-220AC Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Terminals: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: As marked
- ✧ High temperature soldering: 260℃/10 seconds/.16",(4.06mm) from case
- ✧ Weight: 1.9 grams

Dimensions in inches and (millimeters)



Marking Diagram

SFA160XG	= Specific Device Code
G	= Green Compound
Y	= Year
WW	= Work Week

Maximum Ratings and Electrical Characteristics

Rating at 25 ℃ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%

Type Number	Symbol	SFA 801G	SFA 802G	SFA 803G	SFA 804G	SFA 805G	SFA 806G	SFA 807G	SFA 808G	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	500	600	V
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	350	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	500	600	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	8								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	125								A
Maximum Instantaneous Forward Voltage (Note 1) @ 8 A	V_F	0.975				1.3		1.7		V
Maximum Reverse Current @ Rated VR T_A=25 ℃ T_A=100 ℃	I_R	10 400								uA
Maximum Reverse Recovery Time (Note 2)	Trr	35								nS
Typical Junction Capacitance (Note 3)	Cj	100				60				pF
Typical Thermal Resistance	$R_{\theta JC}$	4								^{O}C/W
Operating Temperature Range	T_J	- 65 to + 150								^{O}C
Storage Temperature Range	T_{STG}	- 65 to + 150								^{O}C

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

Note 2: Reverse Recovery Test Conditions: I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

TAIWAN SEMICONDUCTOR

RATINGS AND CHARACTERISTIC CURVES (SFA801G THRU SFA808G)

FIG.1 FORWARD CURRENT DERATING CURVE

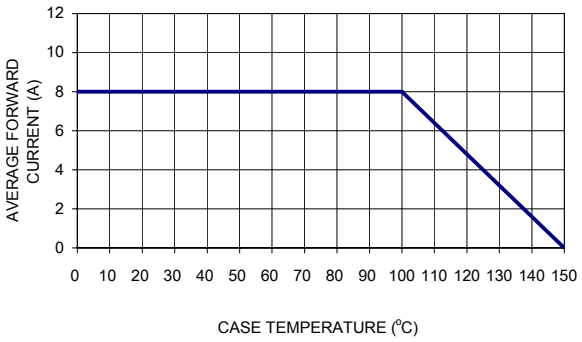


FIG. 2 TYPICAL REVERSE CHARACTERISTICS

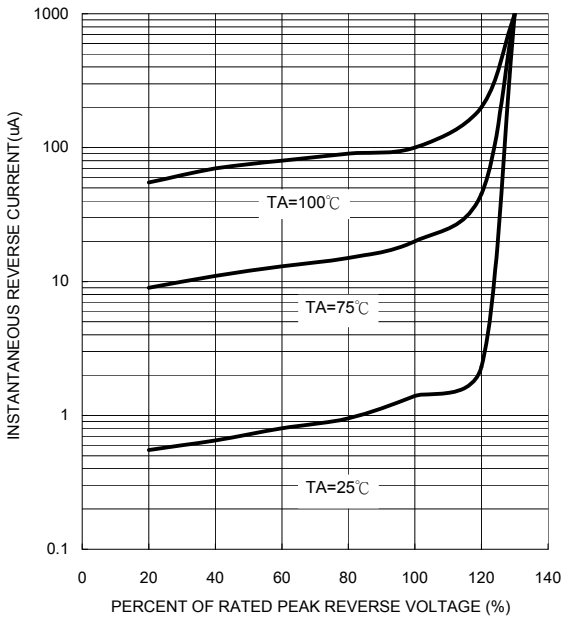


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

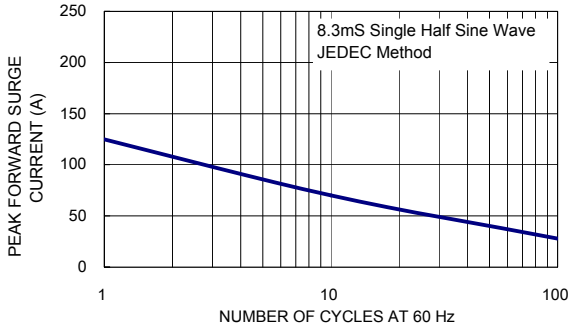


FIG. 5 TYPICAL FORWARD CHARACTERISRICS

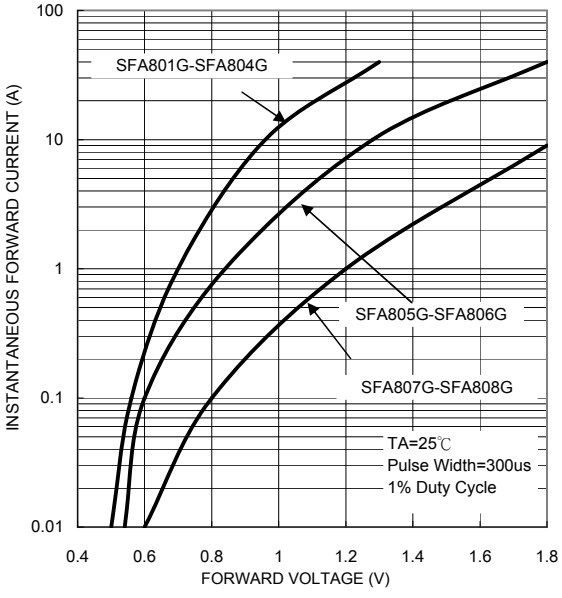


FIG. 4 TYPICAL JUNCTION CAPACITANCE

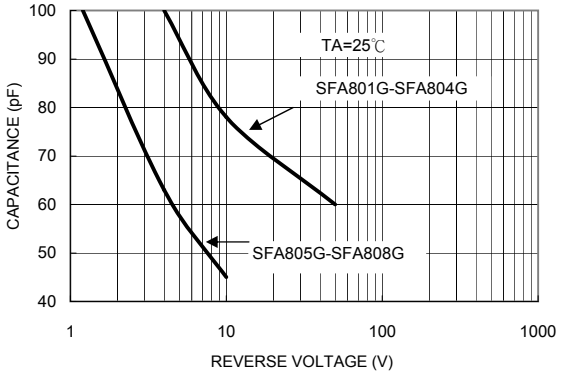


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

